L Number	Hits	Search Text	DB	Time stamp
1	2729515	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 15:30
2	62	(memory or storage) and (sinusoid$5 or trapezoid$5 or rectangular) with read$5 with (control adj gate or substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 15:37
3	0	(memory or storage) and (sinusoid$5 or trapezoid$5 or rectangular) with read$5 with (control adj gate or substrate) with noise	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 15:38
4	15	(memory or storage) and (sinusoid$5 or trapezoid$5 or rectangular) with read$5 with (control adj gate or substrate) and noise	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 15:38

L Number	Hits	Search Text	DB	Time stamp
1	2729515	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 13:49
2	369	(memory or storage) and (voltage or potential or level) with read$5 with variable with time	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 13:51
3	44	((memory or storage) and (voltage or potential or level) with read$5 with variable with time) and (voltage or potential or level) with cell with variable with time	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 14:07
4	6	(((memory or storage) and (voltage or potential or level) with read$5 with variable with time) and (voltage or potential or level) with cell with variable with time) and noise	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 14:07

L Number	Hits	Search Text	DB	Time stamp
1	2729515	memory or storage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 10:38
2	66	(memory or storage) and read$5 with cell with reduc$5 with noise with voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 11:15
3	23	((memory or storage) and read$5 with cell with reduc$5 with noise with voltage) and (nonvolatile or non-volatile or floating adj gate or flash)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 10:54
4	10	(memory or storage) and read$5 with cell with reduc$5 with noise with potential	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/27 11:16